

- BRS:
- BRS:
- BRS:
- BRS: (float33 adj gate) same (control adj gate)
- BRS:
- BRS:
- Pending
- Active
 - L1:[181/09/945498]
 - L2:[181/09/942134]
 - L3:[181/09/945507]
 - L4:[151/08/945512]
 - L5:[181/08/945554]
 - L6:[28112345]
 - L7:[11248] ((asymmetri\$4 graded) near2 [metal tunnel\$3]) with (metal perovskite supe
 - L8:[191] ((asymmetri\$4 graded) near2 [tunnel\$3]) with (metal perovskite superlattice)
 - L9:[18222889] tunnel\$4 intergate Inter adj gate
 - L10:[2817 with 9]
 - L11:[281810]
 - L12:[181] II not 8

D:\[C:\] \[F:\] \[G:\] \[H:\]

D:\[C:\] \[F:\] \[G:\] \[H:\]

II not 8

03/31/2005

	U	Inventor	Document ID	Issue Date	Page	Title	Current RR	Current IHC
1	c	AHN, KY et al	US 20050023895A	20050203	37	Flash memory array for personal computers, digital cameras, or wireless phones, has control gate that is separated from floating gate by asymmetrical io.		
2	c	AHN, KY et al	US 20050023803A	20050203	92	Flash memory array for personal computers, digital cameras, or wireless phones, has control gate that is separated from floating gate by asymmetrical io.		
3	c	AHN, KY et al	US 20050023802A	20050203	37	Flash memory array for personal computers, digital cameras, or wireless phones, has control gate separated from floating gate by asymmetrical low tunnel		
4	m	AHN, KY et al	US 20030048866A	20030313	39	Floating gate transistor for memory array used in programmable logic array, comprises control gate enclosing floating gate, and is separated from floating ga		
5	m	AHN, KY et al.	US 20030042527A	20030306	38	Depletion mode floating gate transistor for flash memory, has control gate separated from floating gate by asymmetric metal oxide made low tunnel barri		
6	m	CHEN, Yet al	CH 1327099 A	20040908	RA	Setting method and device for surface ion body induced photon resonance tunnelling type one-dimensional photonic band gap structure		
7	m	Higureshi; Hitoshi	US 5848559 A	19970708	24	Single-electron tunnelling logic device	320/198	297/31;
8	c	MARKS, Alan M.	EP 1724644 A	19960226	33	Penit diode and applications - has sub-micron metal cylinder with asymmetric tunnel junction and reflection step		257/E28.82;
9	c	Marks; Alan M.	US 5269238 A	19931207	13	Monomolecular resist and process for beamwriter	430/288	
10	c	Marks; Alan M.	US 4972094 A	19901120	15	Lighting devices with quantum electric/light power converters	307/150	257/88;
								257/E26.02;